



» 整流管芯片 | Diode Chips

标准:

- 每片芯片全部在 T_{JM} 下测试, 严格禁止抽检
- 产品参数一致性极佳

Standard:

- Every chips are tested at T_{JM} , random inspections are strictly prohibited.
- Excellent consistency of the chips' parameters

特点:

- 通态压降低
- 具有很强的抗热疲劳能力
- 阴极铝层厚度 10 微米以上
- 台面双层保护

Features:

- Low forward voltage
- Strong thermal fatigue resistance
- The thickness of cathode aluminum layer is above $10\text{ }\mu\text{m}$
- Double layer protections on mesa



芯片直径	芯片厚度	电压范围	阴极外径	结温
Diameter	Thickness	Voltage	Cathode Out Dia.	T_{jm}
mm	mm	V	mm	$^{\circ}\text{C}$
17	1.5 ± 0.1	≤ 2600	12.5	150
23.3	1.95 ± 0.1	≤ 2600	18.5	150
	2.15 ± 0.1	4200-5500	16.5	150
24	1.5 ± 0.1	≤ 2600	18.5	150
25.4	1.4-1.7	≤ 3500	19.5	150
29.72	1.95 ± 0.1	≤ 2600	25	150
	1.9-2.3	2800-5500	23	150
32	1.9 ± 0.1	≤ 2200	27.5	150
	2 ± 0.1	2400-2600	26.3	150
35	1.8-2.1	≤ 3500	29	150
	2.2 ± 0.1	3600-5000	27.5	150
36	2.1 ± 0.1	≤ 2200	31	150
38.1	1.9 ± 0.1	≤ 2200	34	150
40	1.9-2.2	≤ 3500	33.5	150
	2.2-2.5	3600-6500	31.5	150
45	2.3 ± 0.1	≤ 3000	39.5	150
	2.5 ± 0.1	3600-4500	37.5	150
50.8	2.4-2.7	≤ 4000	43.5	150
	2.8 ± 0.1	4200-5000	41.5	150
55	2.4-2.8	≤ 4500	47.7	150
	2.8-3.1	5200-6500	44.5	150
63.5	2.6-3.0	≤ 4500	56.5	150
	3.0-3.3	5200-6500	54.5	150
70	2.9-3.1	≤ 3200	63.5	150
	3.2 ± 0.1	3400-4500	62	150
76	3.4-3.8	≤ 4500	68.1	150
89	3.9-4.3	≤ 4500	80	150
99	4.4-4.8	≤ 4500	89.7	150